

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) V = 10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Ι _D	9.5 7.6	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	l _D	35 28	Α
Maximum Continuous Body Diode Forward Current (Note 5)		Is	2	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	80	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dawer Dissination (Note 5)	T _A = +25°C	0	2.2	- w	
Total Power Dissipation (Note 5)	T _C = +25°C	P_{D}	30		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Devi	57		
	t<10s	$R_{\theta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	4.2			
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

$\textbf{Electrical Characteristics} \ (\textcircled{a}T_{A} = +25^{\circ}C, \ unless \ \ otherwise \ specified.)$

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						•
Drain-Source Breakdown Voltage	BV _{DSS}	80	_	_	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 64V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						•
Gate Threshold Voltage	V _{GS(th)}	1	1.5	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	0	_	13	16	mΩ	V _{GS} = 10V, I _D = 12A
Static Diain-Source On-Resistance	R _{DS(ON)}	_	14	22		$V_{GS} = 6V, I_D = 6A$
Diode Forward Voltage	V_{SD}	_	0.9	1.2	V	V _{GS} = 0V, I _S = 12A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	_	1949	_	pF	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	_	177	_		
Reverse Transfer Capacitance	C _{rss}	_	10	_		
Gate resistance	R _g	_	0.7	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15	_		
Total Gate Charge (V _{GS} = 10V)	Qg	_	34	_	-0	V _{DS} = 40V, I _D = 12A
Gate-Source Charge	Q _{gs}	_	6	_	nC	
Gate-Drain Charge	Q _{gd}	_	4.5	_		
Turn-On Delay Time	t _{D(on)}	_	4.9	_		V _{DD} = 40V, V _{GS} = 10V,
Turn-On Rise Time	t _r	_	3.8	_		
Turn-Off Delay Time	t _{D(off)}	_	16.5	_	nS	$I_D = 12A$, $R_G = 1.6\Omega$,
Turn-Off Fall Time	t _f	_	3.5	_	1	
Body Diode Reverse Recovery Time	t _{rr}	_	30.2	_	nS	100 1111 10001
Body Diode Reverse Recovery Charge	Q _{rr}	_	34.6	_	nC	-I _F = 12A, di/dt = 100A/μs

Notes:

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5. $R_{\theta JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. $R_{\theta JC}$ is guaranteed by design while R_{BJA} is determined by the user's board design.

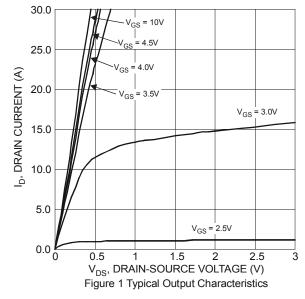
6. Short duration pulse test used to minimize self-heating effect.

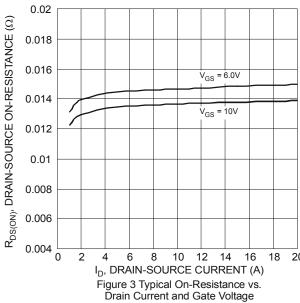
7. Guaranteed by design. Not subject to product testing.

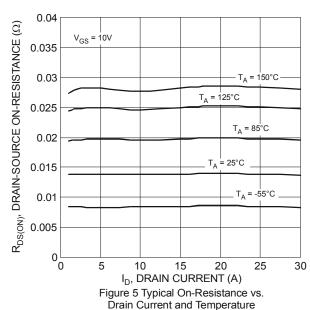
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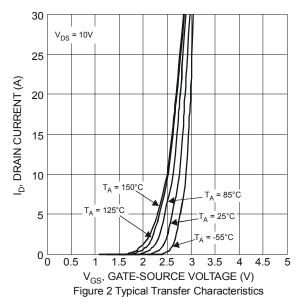
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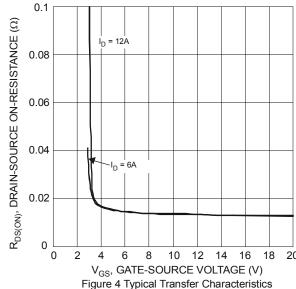












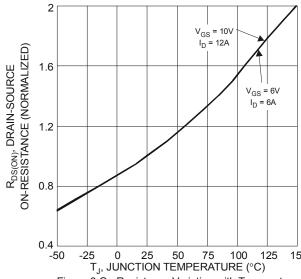
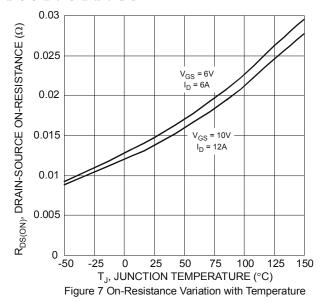
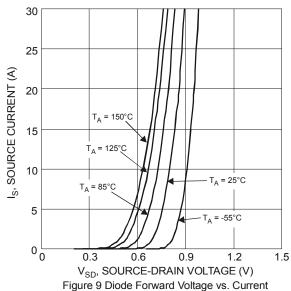
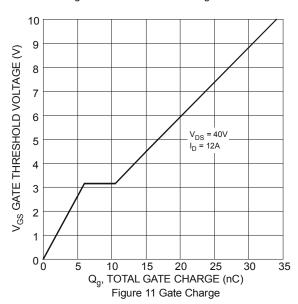


Figure 6 On-Resistance Variation with Temperature









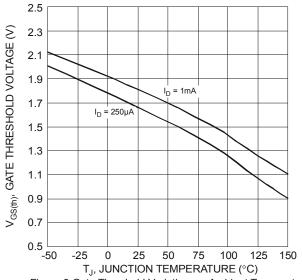
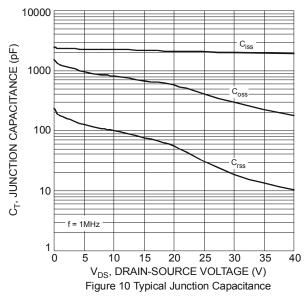
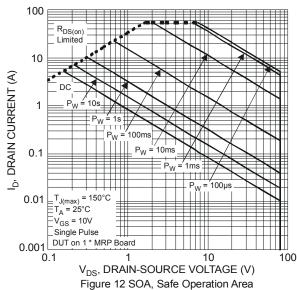
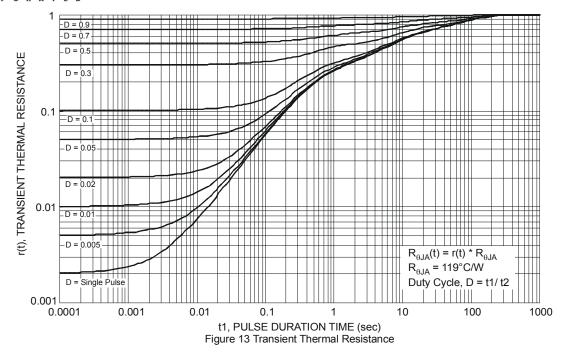


Figure 8 Gate Threshold Variation vs. Ambient Temperature



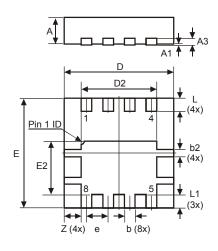






Package Outline Dimensions

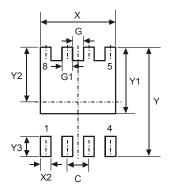
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	1	_	0.203		
b	0.27	0.37	0.32		
b2	-	_	0.20		
L	0.35	0.45	0.40		
L1	1	_	0.39		
е	_	_	0.65		
Z	1	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420



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